





ROHS



Features

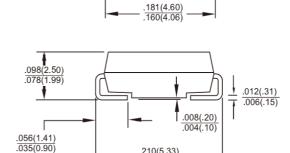
- ♦ Glass passivated junction chip.
- ♦ For surface mounted application
- ♦ Low forward voltage drop
- ♦ Low profile package
- Built-in stain relief, ideal for automatic placement
- ♦ Fast switching for high efficiency
- High temperature soldering: 260°C/10 seconds at terminals
- Plastic material used carries Underwriters Laboratory Classification 94V-0
- Green compound with suffix "G" on packing code & prefix "G" on datecode

Mechanical Data

- ♦ Case: Molded plastic
- ♦ Terminal: Pure tin plated, lead free
- ♦ Polarity: Indicated by cathode band
- ♦ Packing: 12mm tape per EIA STD RS-481
- ♦ Weight: 0.064 grams

SMA/DO-214AC .062(1.58) .050(1.27) .111(2.83) .090(2.29)

1.5 AMPS High Efficient Surface Mount Rectifiers



Dimensions in inches and (millimeters)

.210(5.33) .195(4.95)

Marking Diagram HS2XA = Specific Device Code G = Green Compound Y = Year M = Work Month

Maximum Ratings and Electrical Characteristics

Rating at 25 $^{\circ}$ C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	HS 2AA	HS 2BA	HS 2DA	HS 2FA	HS 2GA	HS 2JA	HS 2KA	HS 2MA	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	300	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	210	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	300	400	600	800	1000	V
Maximum Average Forward Rectified Current	I _{F(AV)}	1.5								Α
Peak Forward Surge Current, 8.3 ms Single Half Sinewave Superimposed on Rated Load (JEDEC method)	I _{FSM}	50								Α
Maximum Instantaneous Forward Voltage (Note 1) @ 1.5A	V _F		1.0 1.3			1.7		٧		
Maximum Reverse Current @ Rated VR $_{\rm A}$ =25 $^{\circ}{\rm C}$ $_{\rm A}$ =125 $^{\circ}{\rm C}$	I _R	5 100								uA
Maximum Reverse Recovery Time (Note 2)	Trr	50					75			nS
Typical Junction Capacitance (Note 3)	Cj	50					30		pF	
Typical Thermal Resistance	$R_{\theta jA}$	80							°C/W	
Operating Temperature Range	TJ	- 55 to + 150							οС	
Storage Temperature Range	T _{STG}	- 55 to + 150								οС

Note 1: Pulse Test with PW=300 usec, 1% Duty Cycle

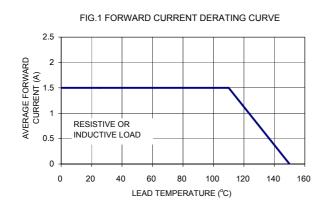
Note 2: Reverse Recovery Test Conditions: I_F =0.5A, I_R =1.0A, I_{RR} =0.25A

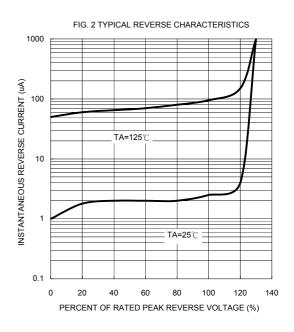
Note 3: Measured at 1 MHz and Applied Reverse Voltage of 4.0V D.C.

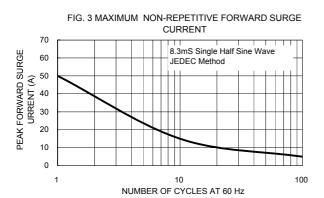
Version:E11



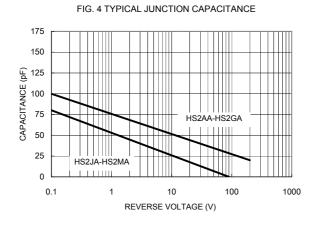
RATINGS AND CHARACTERISTIC CURVES (HS2AA THRU HS2MA)











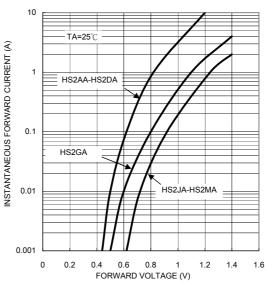


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

